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Docket No.: IN-10

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on the date indicated below.

By: What ohe

Date: December 30, 2005

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applic. No.

09/901,526

Confirmation No: 7099

Applicant

Matthias Förster, et al.

Filed

July 9, 2001

Title

Process for Producing a Microroughness on a Surface

Art Unit

2812

Examiner

Savitri Mulpuri

Docket No.

IN-1078

Customer No. :

24131

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. 1.97(d)

Hon. Commissioner for Patents Alexandria, VA 22313-1450

Sir:

In accordance with 37 C.F.R. 1.98 copies of the following patents and/or publications are cited herewith:

United States Patent No. 5,554,557 (Koh), dated September 10, 1996;

United States Patent No. 5,290,729 (Hayashide, et al.), dated March 1, 1994;

European Patent Application EP 0 448 374 A1 (Watanabe, et al.), dated September 25, 1991;

Hayashide, et al.: "Fabrication of Storage Capacitance-Enhanced Capacitors with a Rough Electrode", Japanese Journal of Applied Physics, Tokyo, JP, 1990, XP 000178146, pp. 869-872;

Yoshimaru, et al.: "Rugged Surface Poly-Si Electrode and Low Temperature Deposited Si₃N₄ for 64Mbit and Beyond STC DRAM Cell", 1990 IEEE, XP

10554581A, pp. 659-662;

European Search Report dated October 31, 2005.

In accordance with 37 C.F.R. 1.97(e) the undersigned herewith states that each item of information contained in the information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the information disclosure statement.

If no translation of pertinent portions of any foreign language patents or publications mentioned above is included with the aforementioned copies of those applications, patents and/or publications, it is because no existing translation is readily available to the applicant.

In accordance with 37 C.F.R. 1.97 (e), consideration of this Information Disclosure Statement is requested.

Enclosed is the fee in the amount of \$180.00.

Respectfully submitted,

For Applicant

WERNER H. STEMER REG. NO. 34,956

Date: December 30, 2005

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U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))

Attorney Docket No.: Applic. No. IN-1078 09/901,526

Applicant

Matthias Förster, et al.

Filing Date July 9, 2001 **Group Art Unit**

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U.S. PATENT DOCUMENTS

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EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
	Α	5,554,557	9/1996	Koh			
	В	5,290,729	3/1994	Hayashide, et al.			
	С						
	D						
	E						
	F						
	G						
	Н						

FOREIGN PATENT DOCUMENT

	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS_	TRANSL. YES NO	
J	0 448 374 A1	9/1991	Europe				
K							
L							
M							
N							

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

- O Hayashide, et al.: "Fabrication of Storage Capacitance-Enhanced Capacitors with a Rough Electrode", Japanese Journal of Applied Physics, Tokyo, JP, 1990, XP 000178146, pp. 869-872
- P Yoshimaru, et al.: "Rugged Surface Poly-Si Electrode and Low Temperature Deposited Si₃N₄ for 64Mbit and Beyond STC DRAM Cell", 1990 IEEE, XP 10554581A, pp. 659-662

EXAMINER

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DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.